	Type	L #	Hits	Search Text	DBs	Time Stamp
1	IS&R	L1	10	(("4577215") or ("52_____") or ("4357635") or ("5287636") or ("_414_97") or ("_191444") or ("4587000") or ("5187633") or ("5216269") or ("5634445")).PN.	USPAT; US-PGPUB	2002/07/12 09:30
2	IS&R	L2	39	(("5479992") or ("5_____") or ("45_____") or ("4592___") or ("461_87_") or ("49_42__") or ("4_0309__") or	USPAT; US-PGPUB	2002/07/12 09:30
3	BRS	L6	12	5 not (2 or 1)	USPAT; US-PGPUB	2002/07/12 09:43
4	IS&R	L5	12	(("5____.32") or ("5_953_4") or ("5_17_6__") or ("5_4306_3") or ("5_6_____") or ("5313421") or ("5_1216__") or ("6__276__") or ("4_026___") r or ("5__342__") r or ("5043940") or ("5_1723_8") or ("5_51881")).PN.	USPAT; US-PGPUB	2002/07/12 09:43

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	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Inventor
1	US 5216269 A	19930601	13	Electrically-programmable semiconductor memories with buried injector region	257/319	257/320; 257/185.3; 365/185.31	Middelhoek, Jan et al.
2	US 4577215 A	19860318	8	Dual word line, electrically alterable, nonvolatile floating gate memory device	257/319	365/185.14; 365/185.18	Stewart, Roger G. et al.
3	US 6240015 B1	20010529	14	Method for reading 2-bit ETOX cells using gate induced drain leakage current	365/185.14	365/185.01; 365/185.26	Chi, Min-hwa et al.
4	US 6121100 B1	20010403	21	Nonvolatile memory cell and method for programming and/or verifying the same	365/185.14	365/185.03; 365/185.2; 365/185.22; 365/185.26	Choi, Woong Lim
5	US 6034882 A	20000307	22	Nonvolatile memory cell and method for programming and/or verifying the same	365/185.14	365/185.01; 365/185.28	Choi, Woong Lim
6	US 5751635 A	19980512	79	Read circuits for analog memory cells	365/185.19	327/93; 327/94; 365/185.03; 365/185.2; 365/185.21	Wong, Sau C. et al.
7	US 5587334 A	19950207	11	Method of forming an array of non-volatile sonos memory cells and array of non-volatile sonos memory cells	438/287	438/296; 438/302	Prall, Kirk
8	US 5218569 A	19930608	23	Electrically alterable non volatile memory with n bits per memory cell	365/185.21	365/185.19; 365/185.2; 365/185.22; 365/185.29; 365/186; 365/45	Banks, Gerald

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	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Inventor
1	US 6222762 B1	20010424	37	Multi-state memory	365/185.03	365/185.03; 365/185.03; 365/185.03	Guterman, Daniel C. et al.
2	US 5891861 A	19981222	18	Method of making memory flash memory for multi-level logic	438/261	438/262; 438/266	Lin, Ruel Lian et al.
3	US 5315541 A	19940517	28	EEPROM with split gate source side injection	365/185.18	365/185.03; 365/185.18; 365/185.12; 365/185.22; 365/185.33; 365/184;	Guterman, Daniel C. et al.
4	US 5172338 A	19921215	44	Multi-state EEPROM read and write circuits and techniques	365/185.03	365/185.03; 365/189.07; 365/185; 365/201; 257/327; 257/488; 365/185.03; 365/185.09; 365/185.16;	Mehrotra, Sanjay et al.
5	US 5095344 A	19920310	49	Highly compact EPROM and flash EEPROM devices	257/328	365/185.2; 365/185.23; 365/185.27; 365/185.3; 365/185.31; 365/185.33	Harari, Eliyahou
6	US 5043940 A	19910827	14	Flash EEPROM memory systems having multistate storage cells	365/185.03	365/185.09; 365/185.11; 365/185.18; 365/185.2; 365/185.22; 365/185.25; 365/185.3; 365/185.33; 365/218	Harari, Eliyahou

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	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Inventor
1	US 5838041 A	19981117	15	Nonvolatile semiconductor memory device having memory cell transistor with field region acting as a charge carrier injecting region	257/321	257/326	Sakagami, Eiji et al.
2	5654568 A	19970805	24	Semiconductor device including nonvolatile memories	257/324	257/295; 257/214; 257/326; 257/326	Nakai, Hironobu.
3	US 4461527 A	19840110	8	High density MNOS transistor with ion implant into nitride layer adjacent gate electrode	257/325	257/344; 257/390; 365/178; 365/184	Chen, Yung J. et al.
4	4342035 A	19820727	9	Electrically erasable programmable MNOS read only memory	365/104	257/346; 365/184	Fuc, Chung Kiang
5	US 4057820 A	19771108	15	Dual gate MNOS transistor	257/326	148/Dig.156	Gallagher, Robert C.
6	US 3925904 A	19751209	17	Structure of and the method of processing a semiconductor matrix or MNOS memory elements	257/326	320/106	Cricchi, James Ronald et al.